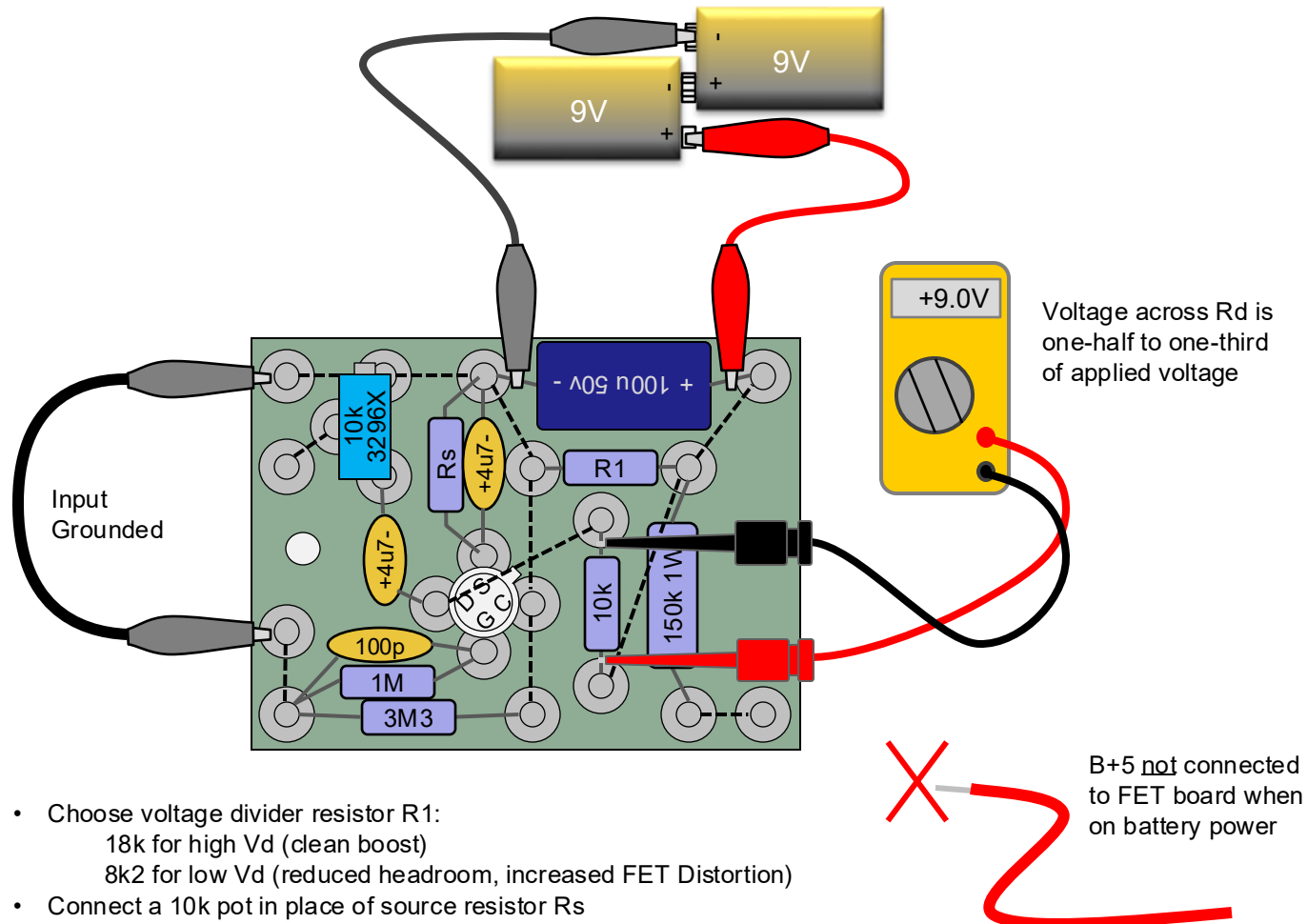


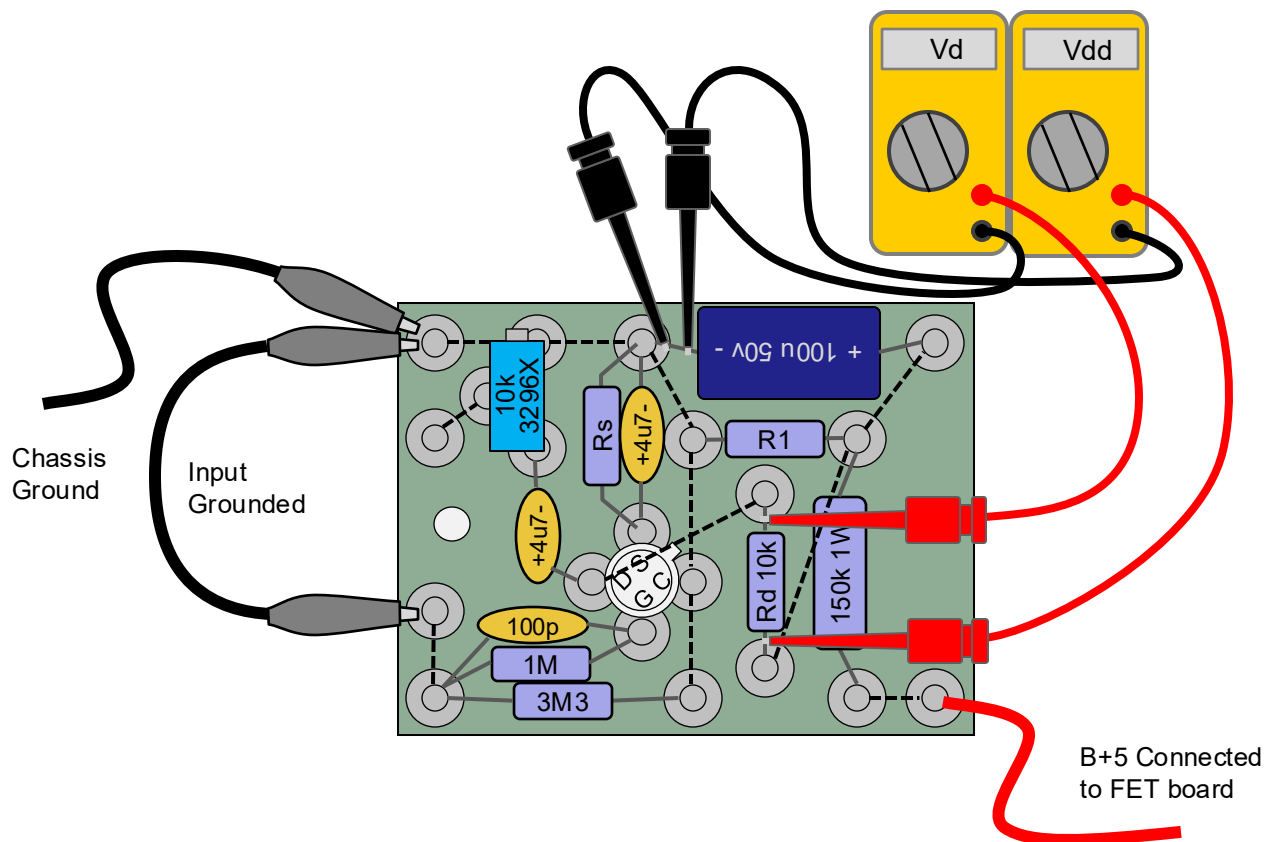
ODS FET Setup Using 9V Batteries



- Choose voltage divider resistor R_1 :
18k for high V_d (clean boost)
8k2 for low V_d (reduced headroom, increased FET Distortion)
- Connect a 10k pot in place of source resistor R_s
- For high V_d , apply +18V V_{dd} using series-connected 9V batteries across R_1
- For low V_d , apply +9V V_{dd} using a single 9V battery across R_1
- Adjust R_s pot for $V_{dd}/V_d = 2.0$ for high V_d , 3.0 for low V_d (R_s will typically be ~2-4k)
- Measure pot value and replace with a fixed resistor for R_s
- Connect FET board to chassis ground and B+5 (~300V)
- Verify V_{dd} and V_{dd}/V_d are in the desired ranges

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Rev 1 May, 2025

ODS FET Setup Using B+5



- Choose value for voltage divider resistor R1:
18k for high V_d (clean boost)
8k2 for low V_d (reduced headroom, increased FET distortion)
- Connect a 10k pot in place of source resistor R_s
- Connect chassis ground and B+5 (~300V) to FET board
- Adjust 10k R_s pot for $V_{dd}/V_d = 2.0$ for maximum headroom, or up to 3.0 for more FET distortion content (R_s range will typically be ~2-4k)
- Measure R_s pot value and replace with fixed resistor for R_s

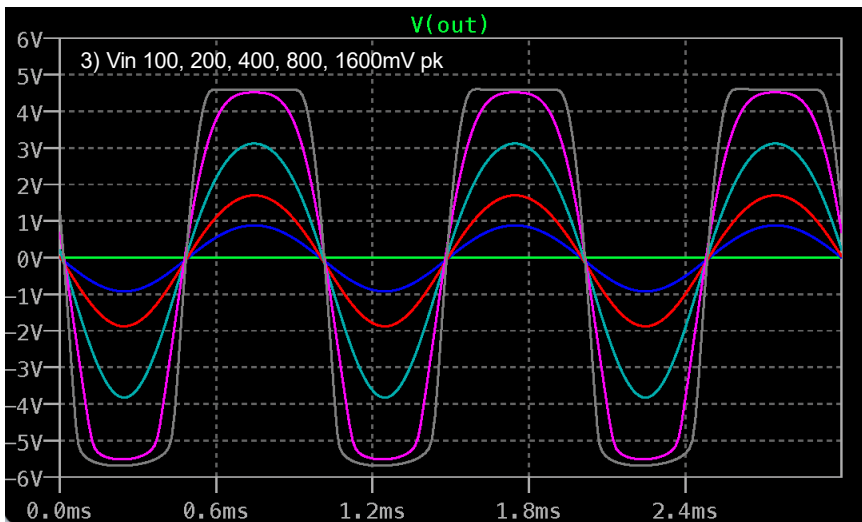
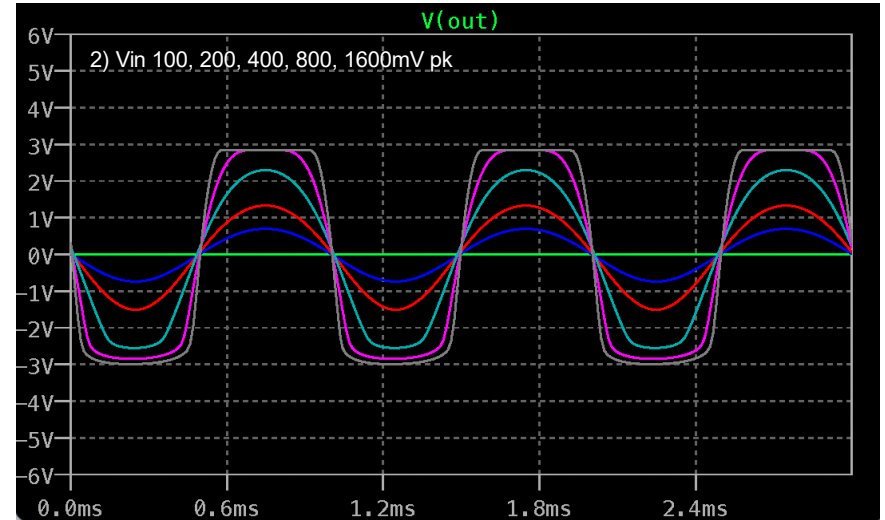
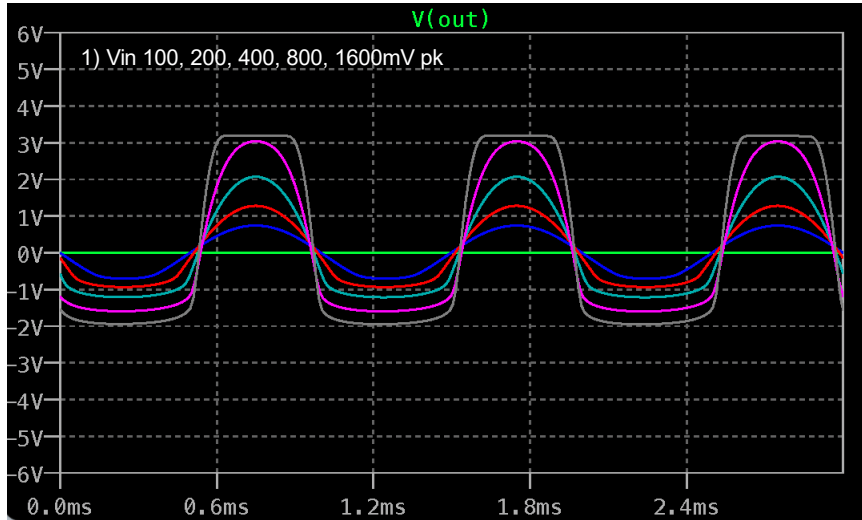
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Bias and Vdd Effect on ODS FET Output Waveform at Constant B+5 Voltage

Case 1: Based on voltage measurements from a Dumble amp with NTE452 FET (2N4416 simulation is a close match).

Case 2: Same configuration as Case 1 with Rs adjusted to drop half of supply voltage across Rd ($V_{dd}/V_d = 2$) to center bias.

Case 3: B+5 divider adjusted to get ~18V Vdd, Rs adjusted to get $V_{dd}/V_d = 2$ for center bias.



FET	2N4416		
Case	1	2	3
B+5	304	304	304
R	150k	150k	150k
R1	8k2	8k2	18k
Rd	10k	10k	10k
Rs	3k3	4k07	2k32
Vd	3.72	5.67	8.79
Vdd	10.49	11.35	17.91
Vdd/Vd	2.82	2.00	2.04
Vs	2.24	2.3	2.12
1kHz Gain, dB	18	17.4	19.2
THD, % (V_{in} 200mV)	16.56	5.89	4.44
-3dB, Hz	63	57	72
MPManning			2021.01.30